SiNx Films, Grown using Unaxis ICP Tool with 100% SiH_4 as well as PECVD Tool, Characterizations						
	Medium-Stress SiN_x (Bias Power=50 W)			Low-Stress SiN_x (Bias Power=120W)		
	100 °C (ICP)	**250 °C (ICP)**	**250 °C (PECVD)**	**100 °C (ICP)**	**250 °C (ICP)**	**250 °C (PECVD)**
Refractive Index	2.01	2.02	1.96	2	2	1.96
Deposition Rate (nm/min)	39.7	38.5	~13	35	32.5	~13
Buffered HF Etch Rate (nm/min)	44.1	31.8	36	37.4	38.1	36
Stress, MPa (~200 nm film on Si substrate)	-451	-556	260	-195	-245	260